LISTING OF CLAIMS:

The present listing of claims replaces all previous versions and listings in the present application.

Please cancel claims 18, 26-37 and 39-40 and add new claims 41-45.

1. – 14. (Canceled)

15. (Currently amended) The method according to claim 38, wherein the semiconductor substrate~~, in a region of which the diffusion structure is formed,~~ is a silicon on insulator substrate.

16. (Original) The method according to claim 15, wherein:

the silicon on insulator substrate includes a semiconductor layer formed on an insulating layer; and

the semiconductor layer is equal to or less than five micrometers.

17. (Previously presented) The method according to claim 38, further comprising filling in the trench with borophosphosilicate glass.

18. (Canceled)

19. (Currently amended) The method according to claim 38, wherein the ~~diffusion structure is formed including~~ diffusion regions are rectangle shaped ~~in a rectangular~~.

20. (Currently amended) The method according to claim 38, wherein the prescribed semiconductor component formed in the separating step is an analog component for processing an analog signal.

21. (Original) The method according to claim 20, wherein the analog component is a bipolar transistor.

22. (Currently amended) The method according to claim 38, wherein the prescribed semiconductor component formed in the separating step is a power component for controlling power supply.

23. (Original) The method according to claim 22, wherein the power component is an insulated gate bipolar transistor.

24. (Original) The method according to claim 22, wherein the power component is an LDMOS transistor.

25. (Previously presented) The method according to claim 38, wherein the semiconductor device manufactured by the method is a hybrid IC including different kinds of semiconductor components integrated into a single chip.

26. – 37. (Canceled)

38. (Currently amended) A method for manufacturing a semiconductor device that includes a prescribed semiconductor component ~~of a kind formed in a substrate~~from a standard platform formed on a semiconductor substrate, the method comprising:

forming the platform to include~~a diffusion structure including~~ a plurality of repeated ~~pattern~~patterns of diffusion regions common to various semiconductors components~~the kind~~ in ~~an area of~~ the substrate~~, in which the semiconductor component is to be formed~~ so that units of the diffusion regions are capable of being separated by trenches;

separating ~~a part of the diffusion structure~~ a unit of the diffusion regions that constitutes the prescribed semiconductor component from ~~a surrounding area thereof~~the repeated patterns of diffusion regions by forming ~~a trench for encircling the part of the diffusion structure including at least a part of the repeated pattern of diffusion regions so as to define the semiconductor component including a predetermined size thereof, and to insulate the semiconductor component from the surrounding area after forming the diffusion structure~~trenches; and

connecting a metallization pattern to the semiconductor component.

39. – 40. (Canceled)

41. (New) A method for manufacturing a semiconductor device that includes a plurality of prescribed semiconductor components from a standard platform formed on a semiconductor substrate, the method comprising:

forming the standard platform to include a plurality of repeated patterns of diffusion regions common to various semiconductor components in the substrate so that each unit of the diffusion regions can be separated from another by a trench;

forming trenches around groups of the diffusion regions that constitute the prescribed semiconductor components to separate the groups of the diffusion regions from other ones of the repeated patterns of diffusion regions; and

connecting metallization patterns to the semiconductor components.

42. (New) The method according to claim 41, wherein:

said plurality of prescribed semiconductor components includes a bipolar transistor having an emitter, a collector and a base, and

said repeated patterns of diffusion regions include a first set of diffusion regions for the emitter, the collector and the base.

43. (New) The method according to claim 41, wherein:

said a plurality of prescribed semiconductor components includes a MOS transistor having a source, a gate and a drain, and

said a plurality of repeated patterns of diffusion regions includes a first set of diffusion regions for the source, the gate and the drain.

44. (New) The method according to claim 42, wherein:

said plurality of prescribed semiconductor components further includes a MOS transistor having a source, a gate and a drain;

said plurality of repeated patterns of diffusion regions further includes a second set of diffusion regions for the source, the gate and the drain; and

said first set of diffusion regions is disposed in a first area of the substrate and said second set of diffusion regions is disposed in a second area of the substrate so that each of a size of the first set and a size of the second set can be changed according to an operating condition of the prescribed semiconductor components.

45. (New) The method according to claim 44, wherein:

each of said repeated patterns of diffusion regions is rectangular.